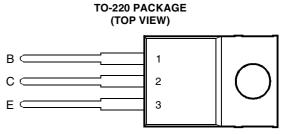
BOURNS®

BDT61, BDT61A, BDT61B, BDT61C NPN SILICON POWER DARLINGTONS

- Designed for Complementary Use with BDT60, BDT60A, BDT60B and BDT60C
- 50 W at 25°C Case Temperature
- 4 A Continuous Collector Current
- Minimum h_{FE} of 750 at 1.5V, 3 A



Pin 2 is in electrical contact with the mounting base.

absolute maximum ratings at 25°C case temperature (unless otherwise noted)

RATING	SYMBOL	VALUE	UNIT	
	BDT61		60	
Collector-base voltage ($I_{\rm E} = 0$)	BDT61A	V	80	v
Collector-base voltage (IE - 0)	BDT61B	V _{CBO}	100	v
	BDT61C		120	
	BDT61		60	
Collector omitter veltage (I)	BDT61A	V	80	v
Collector-emitter voltage ($I_B = 0$)	BDT61B	V _{CEO}	100	v
	BDT61C		120	
Emitter-base voltage	V _{EBO}	5	V	
Continuous collector current	Ι _C	4	A	
Continuous base current	Ι _Β	0.1	A	
Continuous device dissipation at (or below) 25°C case temperature (see Note	P _{tot}	50	W	
Continuous device dissipation at (or below) 25°C free air temperature (see Note 2)			2	W
Operating junction temperature range	Тј	-65 to +150	°C	
Storage temperature range	T _{stg}	-65 to +150	°C	
Operating free-air temperature range	T _A	-65 to +150	°C	

NOTES: 1. Derate linearly to 150°C case temperature at the rate of 0.4 W/°C.

2. Derate linearly to 150°C free air temperature at the rate of 16 mW/°C.

PRODUCT INFORMATION

BDT61, BDT61A, BDT61B, BDT61C NPN SILICON POWER DARLINGTONS



electrical characteristics at 25°C case temperature (unless otherwise noted)

PARAMETER TEST CONDITIONS					MIN	ТҮР	MAX	UNIT	
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C = 30 mA	I _B = 0	(see Note 3)	BDT61 BDT61A BDT61B BDT61C	60 80 100 120			v
I _{CEO}	Collector-emitter cut-off current	$V_{CE} = 30 V$ $V_{CE} = 40 V$ $V_{CE} = 50 V$ $V_{CE} = 60 V$	$I_{B} = 0$ $I_{B} = 0$ $I_{B} = 0$ $I_{B} = 0$		BDT61 BDT61A BDT61B BDT61C			0.5 0.5 0.5 0.5	mA
I _{CBO}	Collector cut-off current	$V_{CB} = 100 V$ $V_{CB} = 120 V$ $V_{CB} = 30 V$ $V_{CB} = 40 V$ $V_{CB} = 50 V$	$I_{E} = 0$	$T_{C} = 150^{\circ}C$ $T_{C} = 150^{\circ}C$ $T_{C} = 150^{\circ}C$ $T_{C} = 150^{\circ}C$	BDT61 BDT61A BDT61B BDT61C BDT61 BDT61A BDT61B BDT61C			0.2 0.2 0.2 2.0 2.0 2.0 2.0	mA
I _{EBO}	Emitter cut-off current	V _{EB} = 5 V	l _C = 0					5	mA
h _{FE}	Forward current transfer ratio	V _{CE} = 3 V	I _C = 1.5 A	(see Notes 3 and 4)		750			
V _{CE(sat)}	Collector-emitter saturation voltage	I _B = 6 mA	I _C = 1.5 A	(see Notes 3 and 4)				2.5	V
V _{BE(on)}	Base-emitter voltage	V _{CE} = 3 V	I _C = 1.5 A	(see Notes 3 and 4)				2.5	V
V _{EC}	Parallel diode forward voltage	I _E = 1.5 A	$I_{B} = 0$					2	V

NOTES: 3. These parameters must be measured using pulse techniques, $t_p = 300 \ \mu$ s, duty cycle $\leq 2\%$.

4. These parameters must be measured using voltage-sensing contacts, separate from the current carrying contacts.

thermal characteristics

PARAMETER			ТҮР	MAX	UNIT
$R_{\theta JC}$	Junction to case thermal resistance			2.5	°C/W
R _{θJA}	Junction to free air thermal resistance			62.5	°C/W

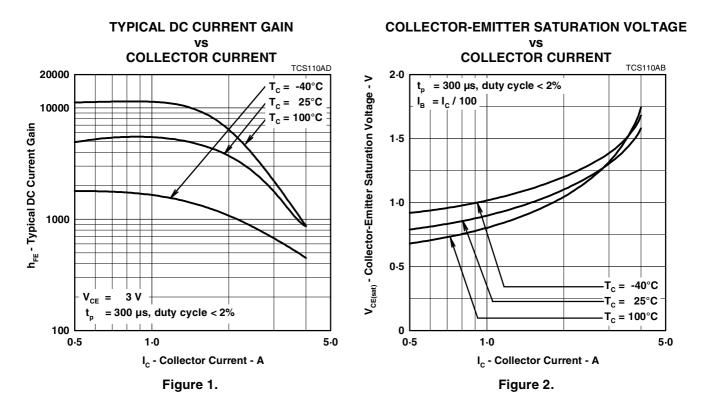
resistive-load-switching characteristics at 25°C case temperature

PARAMETER	TEST CONDITIONS [†]			MIN	ТҮР	MAX	UNIT
t _{on} Turn-on time	I _C = 2 A	I _{B(on)} = 8 mA	I _{B(off)} = -8 mA		1		μs
t _{off} Turn-off time	$V_{BE(off)} = -5 V$	$R_L = 20 \ \Omega$	t_p = 20 μ s, dc \leq 2%		4.5		μs

[†] Voltage and current values shown are nominal; exact values vary slightly with transistor parameters.



TYPICAL CHARACTERISTICS

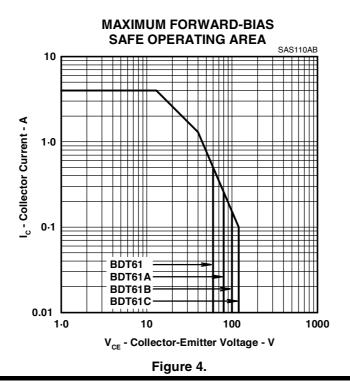


BASE-EMITTER SATURATION VOLTAGE vs **COLLECTOR CURRENT** TCS110AC 3.0 $T_c = -40^{\circ}C$ V_{EE(sat)} - Base-Emitter Saturation Voltage - V $T_c = 25^{\circ}C$ T_c 100°C = 2.5 2.0 1.5 1.0 $= I_c / 100$ I_B = 300 μ s, duty cycle < 2% 0.5 0.5 1.0 5.0 I_c - Collector Current - A Figure 3.

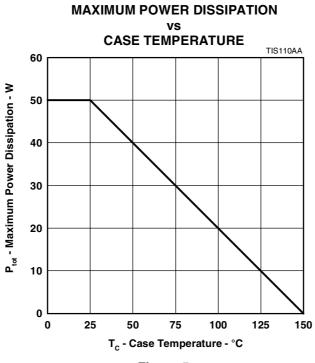
PRODUCT INFORMATION

AUGUST 1993 - REVISED SEPTEMBER 2002 Specifications are subject to change without notice.

MAXIMUM SAFE OPERATING REGIONS









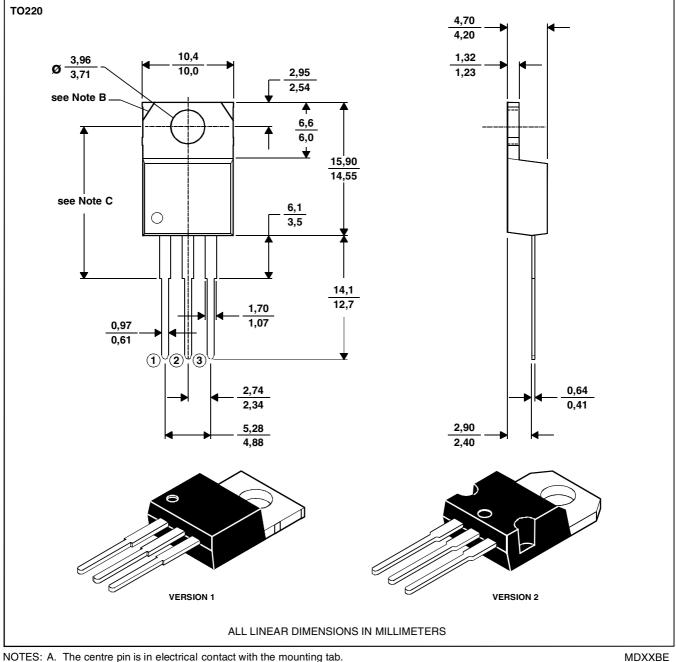
PRODUCT INFORMATION

MECHANICAL DATA

TO-220

3-pin plastic flange-mount package

This single-in-line package consists of a circuit mounted on a lead frame and encapsulated within a plastic compound. The compound will withstand soldering temperature with no deformation, and circuit performance characteristics will remain stable when operated in high humidity conditions. Leads require no additional cleaning or processing when used in soldered assembly.



B. Mounting tab corner profile according to package version.

C. Typical fixing hole centre stand off height according to package version. Version 1, 18.0 mm. Version 2, 17.6 mm.

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